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Sheet 1 of 1

Complete if Known	
Application Number	10/563,105-Conf. #4561
Filing Date	December 30, 2005
First Named Inventor	Misao TAKAKUSAKI
Art Unit	1792
Examiner Name	M. J. Song
Attorney Docket Number	1592-0159PUS1

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS

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Examiner Initials	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[6]
	CA	Mi et al., "Improvement of optical and electronic properties in broken gap mid-wave infrared laser materials," Conference on Lasers and Electro-Optics (CLEO 2001), Technical Digest, Postconference Edition, Baltimore, Md., May 6-11, 2001 {Trends in Optics and Photonics. (Tops)}, US Washington, WA: OSA, US, Vol. 56, pp. 486-487, XP010560097	
	CB	HARPER et al., "Cross-sectional scanning tunneling microscopy characterization of molecular beam epitaxy grown InAs/GaSb/AlSb heterostructures for mid-infrared interband cascade lasers," Journal of Vacuum Science & Technology B: Microelectronicsprocessing and Phenomena, American Vacuum Society, New York, NY, US, Vol. 16, No. 3, May 1, 1998, pg. 1389-1394, XP012006832	
	CC	HASENBERG et al., "Molecular beam epitaxy growth and characterization of broken-gap (type II) superlattices and quantum wells for midwave-infrared laser diodes," Journal of Vacuum Science & Technology B: Microelectronicsprocessing and Phenomena, American Vacuum Society, New York, NY, US, Vol. 18, No. 3, May 1, 2000, pp. 1623-1627, XP012008258	
	CD	DESALVO et al., "Citric Acid Etching of $GaAs_{1-x}Sb_x$, $Al_{0.5}Ga_{0.5}Sb$, and InAs for Heterostructure Device Fabrication," Journal of the Electrochemical Society, Electrochemical Society, Manchester, New Hampshire, US, Vol. 141, No. 12, December 1, 1994, pp. 3526-3531, XP000495786	

Examiner Signature	/Matthew Song/	Date Considered	02/11/2010

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